

Application No. 09/497,508

East Search

3/26/01

Search	L No.	Hits	Text Search			Data Bases
IS&R	L2	1453	((("257/52,55,58,62,63") or ("438/48,482")).CCLS.		3/26/01 11:07	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L3	311	2 and polycrystalline		3/26/01 11:07	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L4	92	3 and (ni au co)		3/26/01 11:10	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L5	4	4 and nucleus		3/26/01 11:11	USPAT; EPO; JPO; Derwent; IBM TDB

Search Result

[illegible]

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Search	L No.	Hits	Text Search			Data Bases
BRS	L1	85678	crystallization		3/26/01 11:22	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L2	2957	1 and polycrystalline		3/26/01 11:22	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L3	1219	2 and (ni au co)		3/26/01 11:23	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L4	125	3 and nucleus		3/26/01 11:24	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L5	106	4 and amorphous		3/26/01 11:24	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L6	74	5 and low adj temperature		3/26/01 11:27	USPAT; EPO; JPO; Derwent; IBM TDB

Search Result

USPAT	Date	Page	Title	CI/Sub	CI/Sub	Inventor
US 4892800 A	19900109	25	Photosensitive member having a photoconductive layer comprising a carbonic film for use in electrophotography	430/85	430/95	Sugata, Masao , et al.
US 5403772 A	19950404	23	Method for manufacturing semiconductor device	438/166	117/8 ; 257/66 ; 438/154 ; 438/30 ; 438/96 ; 438/97	Zhang, Hongyong , et al.
US 5614426 A	19970325	13	Method of manufacturing semiconductor device having different orientations of crystal channel growth	438/150	148/DIG.16 ; 438/166 ; 438/30 ; 438/982	Funada, Fumiaki , et al.
US 5620910 A	19970415	23	Method for producing semiconductor device with a gate insulating film consisting of silicon oxynitride	438/151	438/591 ; 438/762 ; 438/771 ; 438/909	Teramoto, Satoshi
US 5797999 A	19980825	14	Solar cell and method for fabricating the same	136/258	438/97	Sannomiya, Hitoshi , et al.
US 5814835 A	19980929	19	Semiconductor device and method for fabricating the same	257/64	257/347 ; 257/65 ; 257/66	Makita, Naoki , et al.
US 5837569 A	19981117	28	Semiconductor device and method for producing the same	438/166	438/486 ; 438/488	Makita, Naoki , et al.
US 5846320 A	19981208	28	Method for forming crystal and crystal article obtained by said method	117/90	117/105 ; 117/95 ; 427/249.12	Matsuyama, Jinsho , et al.
US 5851860 A	19981222	29	Semiconductor device and method for producing the same	438/166	438/486	Makita, Naoki , et al.